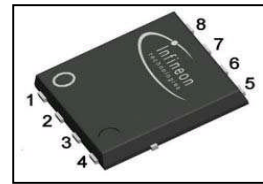


**OptiMOS™3 Power-Transistor**
**Features**

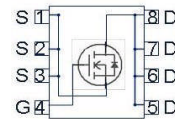
- Optimized for dc-dc conversion
- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant;
- Qualified according to JEDEC<sup>1)</sup> for target application
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	150	V
$R_{DS(on),max}$	52	mΩ
$I_D$	21	A

**PG-TDSON-8**


Type	Package	Marking
BSC520N15NS3 G	PG-TDSON-8	520N15NS


**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	21	A
		$T_C=100\text{ °C}$	14	
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	84	
Avalanche energy, single pulse	$E_{AS}$	$I_D=18\text{ A}, R_{GS}=25\text{ }\Omega$	60	mJ
Gate source voltage	$V_{GS}$		$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	57	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	2.2	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	-	50	

**Electrical characteristics, at  $T_j=25$  °C, unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D=1$ mA	150	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=35$ $\mu$ A	2	3	4	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=120$ V, $V_{GS}=0$ V, $T_j=25$ °C	-	0.01	1	$\mu$ A
		$V_{DS}=120$ V, $V_{GS}=0$ V, $T_j=125$ °C	-	10	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20$ V, $V_{DS}=0$ V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10$ V, $I_D=18$ A	-	42	52	m $\Omega$
		$V_{GS}=8$ V, $I_D=9$ A	-	42	52	
Gate resistance	$R_G$		-	2.1	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=18$ A	11	21	-	S

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu$ m thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> see figure 3

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=75\text{ V},$ $f=1\text{ MHz}$	-	670	890	pF
Output capacitance	$C_{oss}$		-	80	-	
Reverse transfer capacitance	$C_{rss}$		-	3.4	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=75\text{ V}, V_{GS}=10\text{ V},$ $I_D=9\text{ A}, R_G=1.6\ \Omega$	-	7	-	ns
Rise time	$t_r$		-	4	-	
Turn-off delay time	$t_{d(off)}$		-	10	-	
Fall time	$t_f$		-	3	-	

**Gate Charge Characteristics<sup>4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=75\text{ V}, I_D=9\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3.5	4.6	nC
Gate to drain charge	$Q_{gd}$		-	1.5	-	
Switching charge	$Q_{sw}$		-	3	-	
Gate charge total	$Q_g$		-	8.7	12	
Gate plateau voltage	$V_{plateau}$		-	5.2	-	V
Output charge	$Q_{oss}$	$V_{DD}=75\text{ V}, V_{GS}=0\text{ V}$	-	22	29	nC

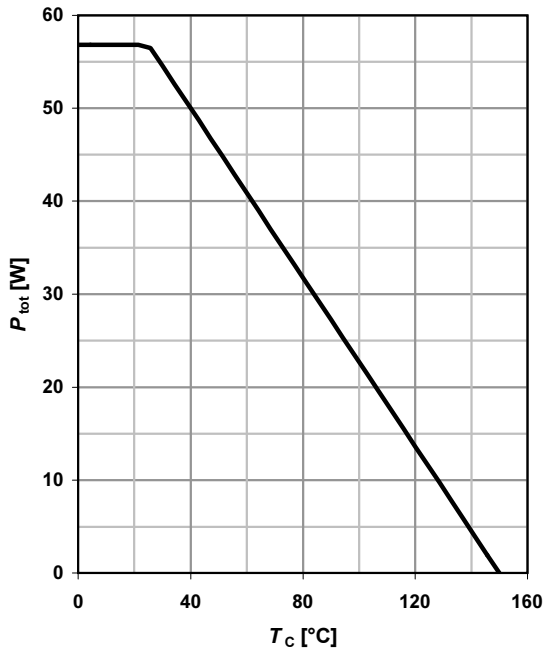
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	21	A
Diode pulse current	$I_{S,pulse}$		-	-	84	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=21\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{ V}, I_F=9\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	66	-	ns
Reverse recovery charge	$Q_{rr}$		-	226	-	nC

<sup>4)</sup> See figure 16 for gate charge parameter definition

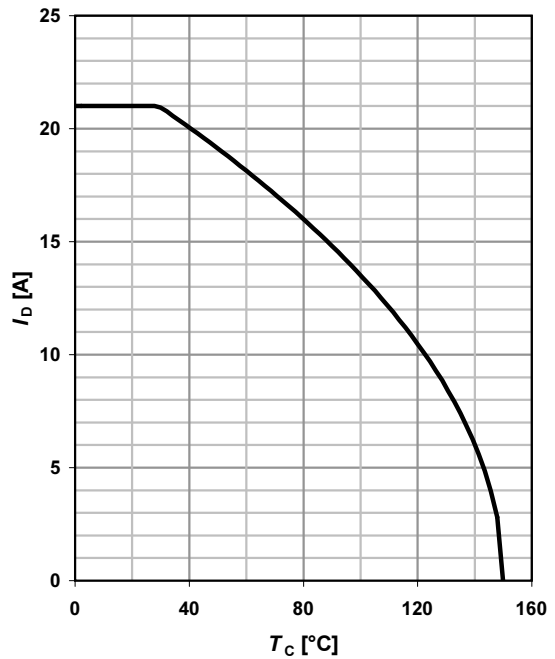
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

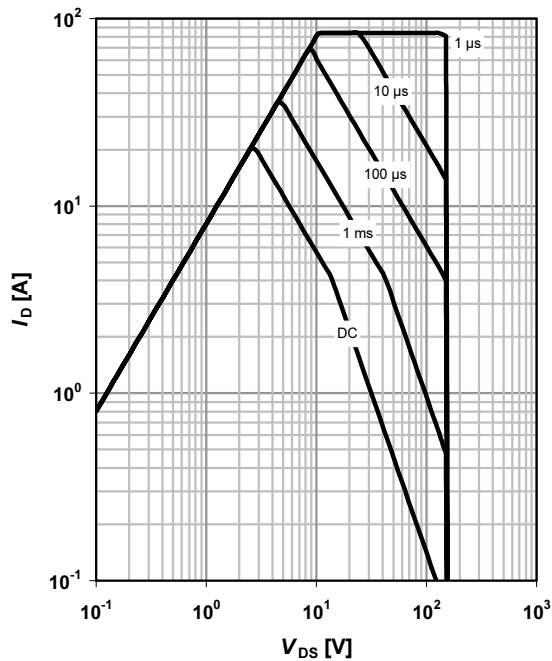
$I_D=f(T_C); V_{GS} \geq 10 V$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25^\circ C; D=0$

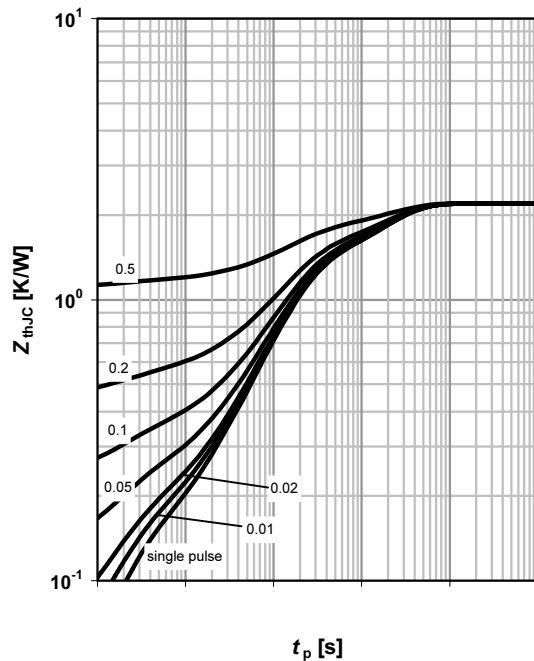
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

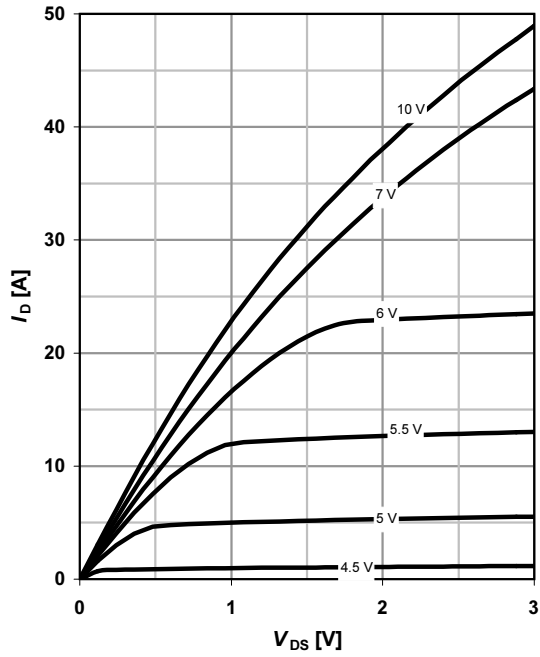
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

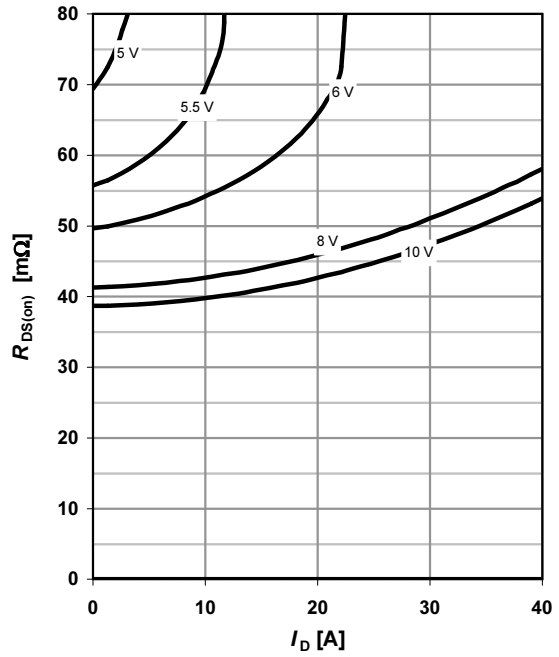
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

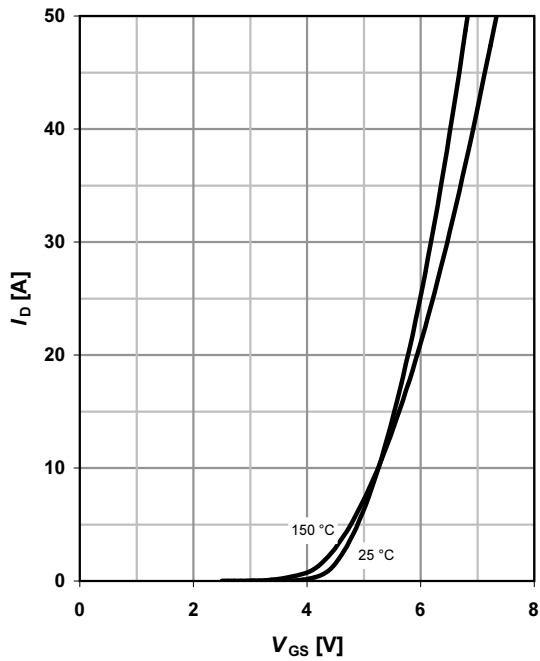
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

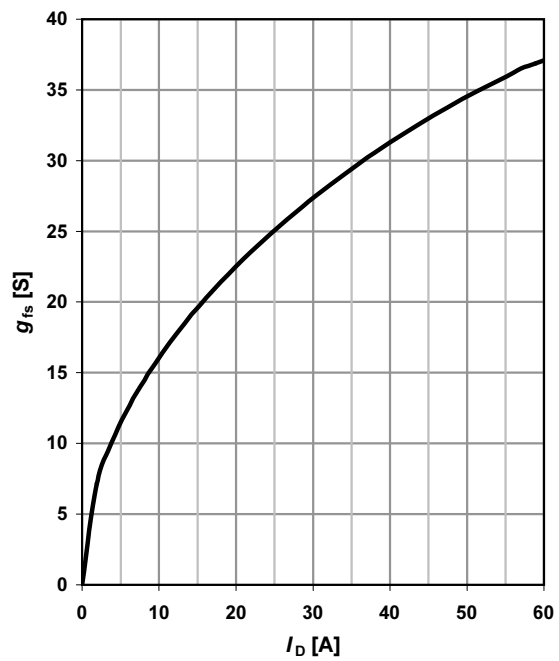
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



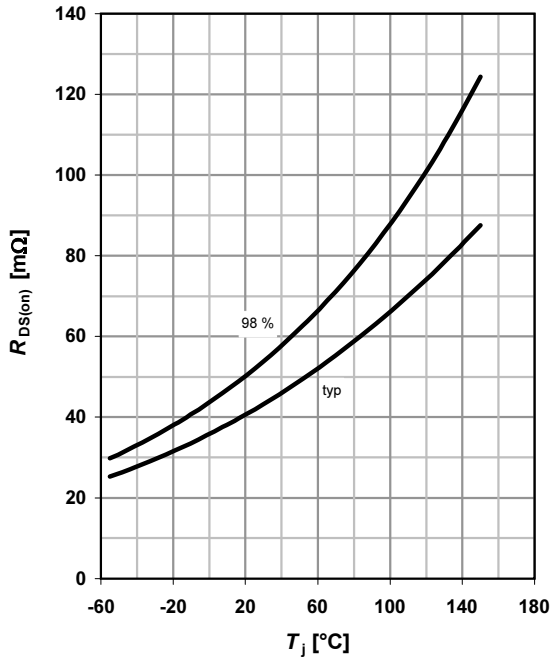
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

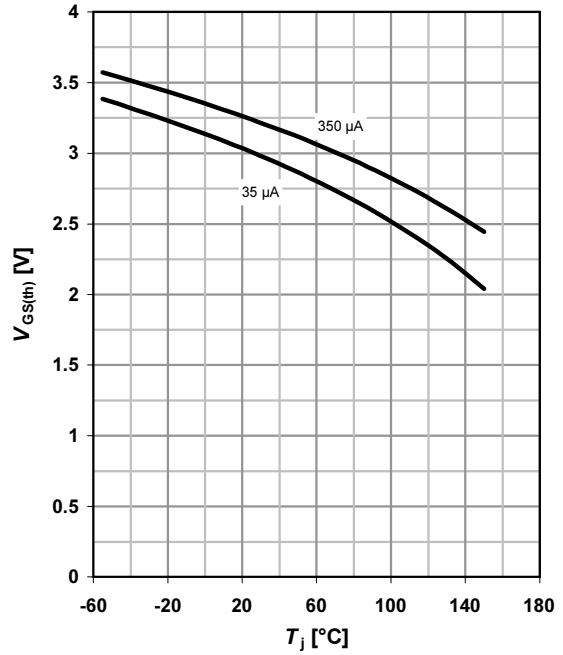
$R_{DS(on)} = f(T_j); I_D = 18 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

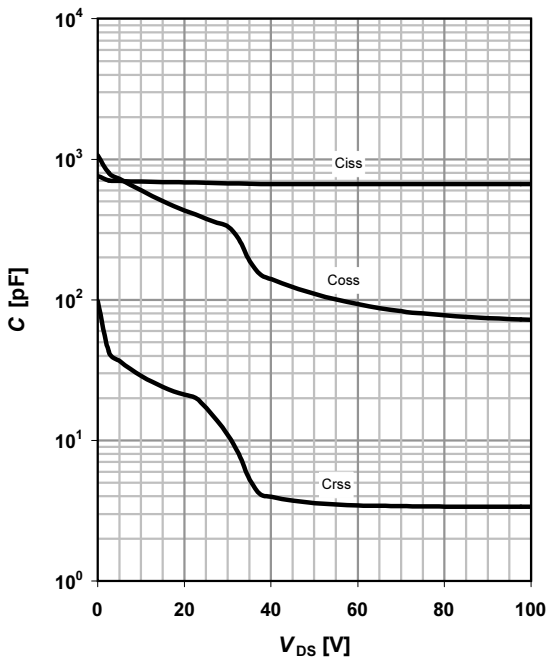
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

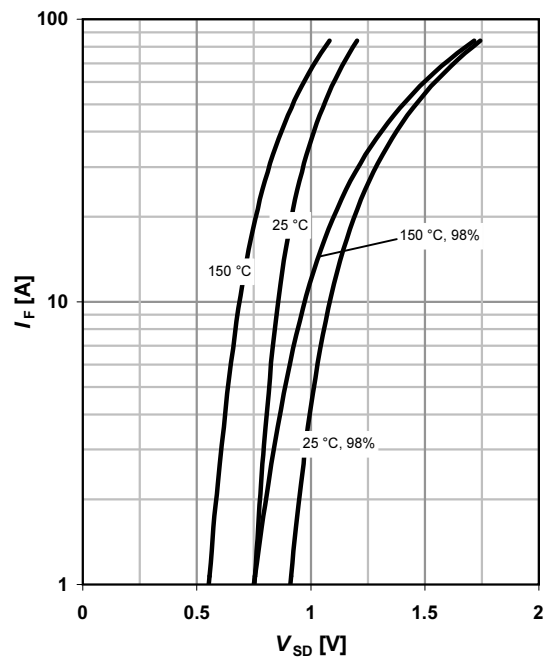
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

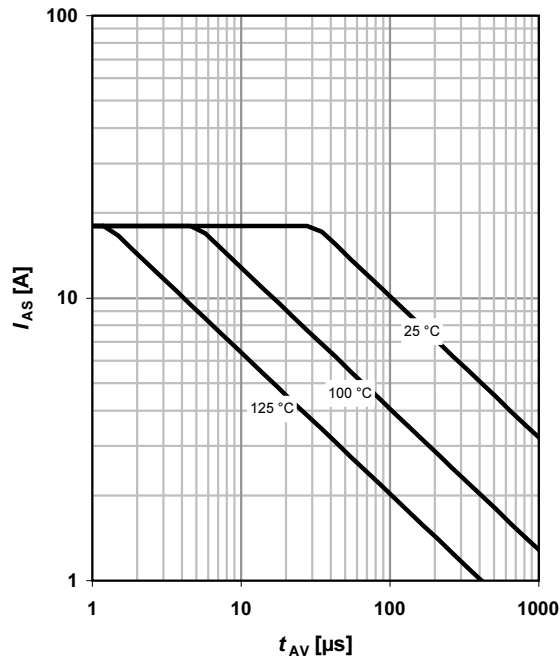
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

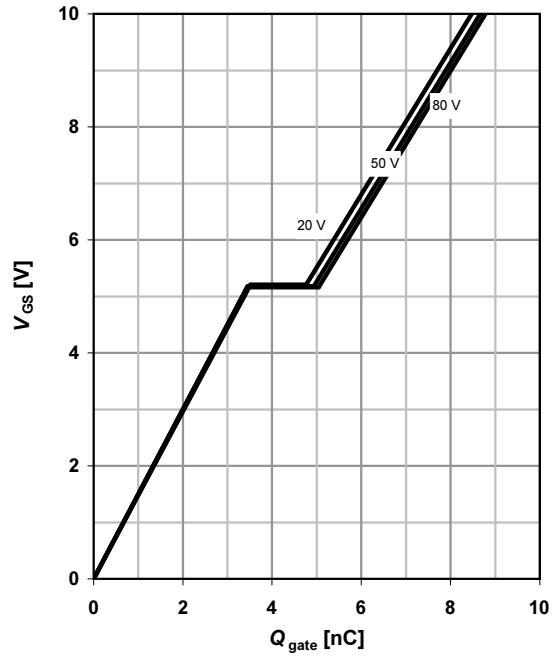
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

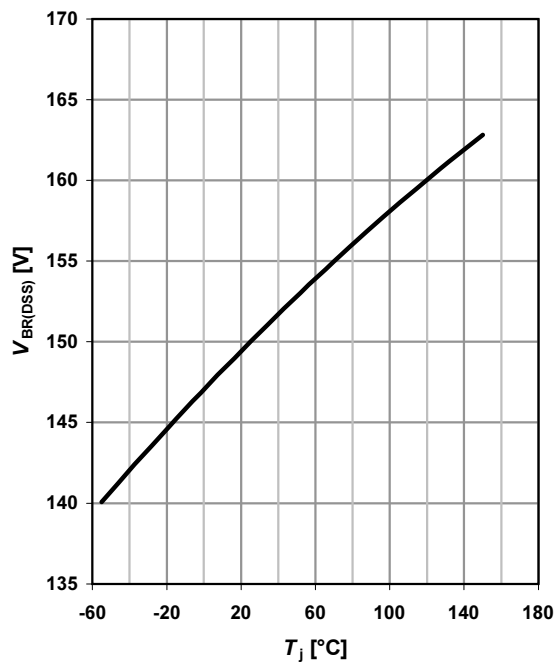
$V_{GS}=f(Q_{gate}); I_D=9 \text{ A pulsed}$

parameter:  $V_{DD}$

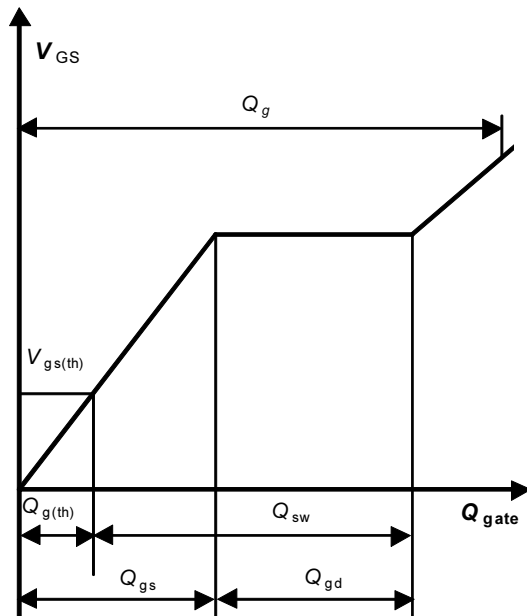


**15 Drain-source breakdown voltage**

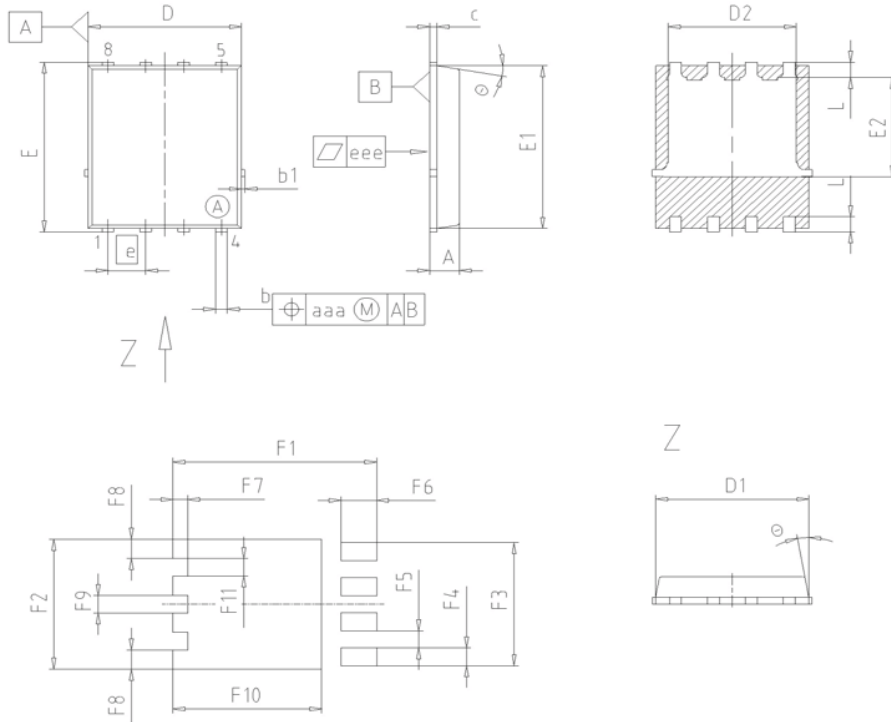
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**



Package Outline: PG-TDSON-8



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.34	0.54	0.013	0.021
b1	0.02	0.22	0.001	0.008
c	0.15	0.35	0.006	0.014
D=D1	4.95	5.35	0.195	0.211
D2	4.20	4.40	0.165	0.173
E	5.95	6.35	0.234	0.250
E1	5.70	6.10	0.224	0.240
E2	3.40	3.80	0.134	0.150
e	1.27		0.050	
N	8		8	
L	0.45	0.65	0.018	0.026
□	8.5°	11.5°	8.5°	11.5°
aaa	0.25		0.010	
eee	0.05		0.002	
F1	6.75	6.95	0.266	0.274
F2	4.60	4.80	0.181	0.189
F3	4.36	4.56	0.172	0.180
F4	0.55	0.75	0.022	0.030
F5	0.52	0.72	0.020	0.028
F6	1.10	1.30	0.043	0.051
F7	0.40	0.60	0.016	0.024
F8	0.60	0.80	0.024	0.031
F9	0.53	0.73	0.021	0.029
F10	4.90	5.10	0.193	0.201
F11	0.53	0.73	0.021	0.029

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